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	12007-0074	10/580,653
	APPLICANT Wolfgang STOLZ et al.	
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	<u>TRANSLATION</u> YES NO PART.
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OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	1.	C. SETIAGUNG et al., "Very Low Threshold Current Density of 1.3 μ m-range GaInNAsSb/GaNAs 5QWs Lasers", The Furukawa Electric Co., Ltd., Yokohama R&D Laboratories, © 2002, IEEE, pgs. 39-40
	2.	E. GOUARDES et al., "GaInAs-GaInNAs-GaInAs Intermediate Layer Structure for Long Wavelength Lasers", <i>IEEE PHOTONICS TECHNOLOGY LETTERS</i> , vol. 14, No. 7, July 2002, pgs. 896-898
	3.	M. KAWAGUCHI et al., "Photoluminescence and Lasing Characteristics of 1.3 μ m GaInNAs/GaAsP/GaAs Strain-compensated Quantum Wells", <i>Compound Semiconductors</i> 2003, International Symposium, August 25-27, 2003, pgs. 72-73
EXAMINER		DATE CONSIDERED
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